

Method Of Forming A Contact On A Silicon-On-Insulator Wafer

ABSTRACT

In a method of the present invention, an intermediate structure having a top surface is provided. An isolation trench is formed in the intermediate structure. Isolation material is deposited over the intermediate structure. The isolation material fills the isolation trench. Excess isolation material extends above the top surface of the intermediate structure. Part of the excess isolation material is removed until there is a predetermined thickness of isolation material remaining on the top surface of the intermediate structure. A contact opening is formed in the isolation material at the isolation trench. The contact opening extends through at least part of the intermediate structure. Contact material is deposited over the isolation material. The contact material fills the contact opening. Excess contact material, if any, that extends above the isolation material is removed. The excess isolation material is removed at least until the top surface of the intermediate structure is reached.